

# Photodiode arrays with amplifiers



S11865-64/-128/-256  
S11866-64-02/-128-02

## Photodiode arrays combined with signal processing IC

The S11865/S11866 series are Si photodiode arrays combined with a signal processing IC chip. X-ray tolerance has been improved compared to the previous products (S8865/S8866 series). The signal processing IC chip is formed by CMOS process and incorporates a timing generator, shift register, charge amplifier array, clamp circuit and hold circuit, making the external circuit configuration simple. A long, narrow image sensor can also be configured by arranging multiple arrays in a row. For X-ray detection applications, types with phosphor sheet affixed on the photosensitive area are also available. As the dedicated driver circuit, the C9118-01 (sold separately) is provided (this circuit does not support the S11865-256).

### Features

- Data rate: 1 MHz max.
- Element pitch: 5 types available
  - S11865-64: 0.8 mm pitch × 64 ch
  - S11865-128: 0.4 mm pitch × 128 ch
  - S11865-256: 0.2 mm pitch × 256 ch
  - S11866-64-02: 1.6 mm pitch × 64 ch
  - S11866-128-02: 0.8 mm pitch × 128 ch
- 5 V power supply operation
- Simultaneous integration by using a charge amplifier array
- Sequential readout with a shift register
- Low dark current due to zero-bias photodiode operation
- Integrated clamp circuit allows low noise and wide dynamic range
- Integrated timing generator allows operation at two different pulse timings
- Types with phosphor sheet affixed on the photosensitive area are available for X-ray detection (S11865-64G/-128G/-256G, S11866-64G-02/-128G-02)

### Applications

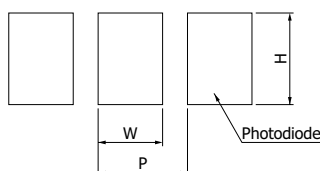
- Long and narrow line sensors
- Line sensors for X-ray detection

### Structure

Parameter	Symbol*1	S11865-64	S11865-128	S11865-256	S11866-64-02	S11866-128-02	Unit
Element pitch	P	0.8	0.4	0.2	1.6	0.8	mm
Element width	W	0.7	0.3	0.1	1.5	0.7	mm
Element height	H	0.8	0.6	0.3	1.6	0.8	mm
Number of elements	-	64	128	256	64	128	-
Effective photosensitive area length	-	51.2	51.2	51.2	102.4	102.4	mm
Board material	-	Glass epoxy					-

\*1: Refer to following figure.

### Enlarged drawing of photosensitive area



KMPDC0072EA

### ➤ Absolute maximum ratings (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Supply voltage	Vdd	-0.3 to +6	V
Reference voltage	Vref	-0.3 to +6	V
Photodiode voltage	Vpd	-0.3 to +6	V
Gain selection terminal voltage	Vgain	-0.3 to +6	V
Master/slave selection voltage	Vms	-0.3 to +6	V
Clock pulse voltage	V(CLK)	-0.3 to +6	V
Reset pulse voltage	V(RESET)	-0.3 to +6	V
External start pulse voltage	V(EXTSP)	-0.3 to +6	V
Operating temperature*2	Topr	-5 to +60	°C
Storage temperature*2	Tstg	-10 to +70	°C

\*2: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

### ➤ Recommended terminal voltage (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	Vdd	4.75	5	5.25	V
Reference voltage	Vref	4	4.5	4.6	V
Photodiode voltage	Vpd	-	Vref	-	V
Gain selection terminal voltage	High gain	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low gain	0	-	0.4	V
Master/slave selection voltage	High level*3	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level*4	0	-	0.4	V
Clock pulse voltage	High level	3.3	Vdd	Vdd + 0.25	V
	Low level	0	-	0.4	V
Reset pulse voltage	High level	3.3	Vdd	Vdd + 0.25	V
	Low level	0	-	0.4	V
External start pulse voltage	High level	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	0	-	0.4	V

\*3: Parallel

\*4: Serial at 2nd or later stages

### ➤ Electrical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(RESET)=5 V]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Clock pulse frequency*5	f(CLK)	40	-	4000	kHz
Line rate*6	S11865-64, S11866-64-02	-	-	14678	lines/s
	S11865-128, S11866-128-02	-	-	7568	
	S11865-256	-	-	3844	
Output impedance	Zo	-	3	-	kΩ
Current consumption	S11865-64, S11866-64-02	-	16	-	mA
	S11865-128, S11866-128-02	-	30	-	
	S11865-256	-	60	-	
Charge amp feedback capacitance	High gain	-	0.5	-	pF
	Low gain	-	1	-	

\*5: Video data rate is 1/4 of clock pulse frequency f(CLK).

\*6: The values depend on the clock pulse frequency.

**Electrical and optical characteristics [Ta=25 °C, Vdd=5 V, V(CLK)=V(RESET)=5 V, Vgain=5 V (High gain), 0 V (Low gain)]**

S11865-64/-128/-256

Parameter	Symbol	S11865-64			S11865-128			S11865-256			Unit	
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.		
Spectral response range	$\lambda$	200 to 1000			200 to 1000			200 to 1000			nm	
Peak sensitivity wavelength	$\lambda_p$	-	720	-	-	720	-	-	720	-	nm	
Dark output voltage*7	Vd	High gain	-	0.01	0.2	-	0.01	0.2	-	0.01	0.2	mV
		Low gain	-	0.005	0.1	-	0.005	0.1	-	0.005	0.1	
Saturation output voltage	Vsat	3.0	3.5	-	3.0	3.5	-	3.0	3.5	-	V	
Saturation exposure*8	Esat	High gain	-	0.8	1.0	-	2.4	3.0	-	15	19	mIx · s
		Low gain	-	1.6	2.0	-	4.8	6.0	-	30	37.5	
Photosensitivity	Sw	High gain	3520	4400	-	1200	1500	-	200	250	-	V/Ix · s
		Low gain	1760	2200	-	600	750	-	100	125	-	
Photoresponse nonuniformity*9	PRNU	-	-	±10	-	-	±10	-	-	±10	%	
Noise*10	N	High gain	-	1.3	2.0	-	1.0	1.5	-	0.8	1.2	mV rms
		Low gain	-	0.7	1.1	-	0.6	0.9	-	0.5	0.75	
Output offset voltage*11	Voffset	-	Vref	-	-	Vref	-	-	Vref	-	V	

S11866-64-02/-128-02

Parameter	Symbol	S11866-64-02			S11866-128-02			Unit	
		Min.	Typ.	Max.	Min.	Typ.	Max.		
Spectral response range	$\lambda$	200 to 1000			200 to 1000			nm	
Peak sensitivity wavelength	$\lambda_p$	-	720	-	-	720	-	nm	
Dark output voltage*7	Vd	High gain	-	0.01	0.2	-	0.01	0.2	mV
		Low gain	-	0.005	0.1	-	0.005	0.1	
Saturation output voltage	Vsat	3	3.5	-	3	3.5	-	V	
Saturation exposure*8	Esat	High gain	-	0.2	0.25	-	0.8	1.0	mIx · s
		Low gain	-	0.4	0.5	-	1.6	2.0	
Photosensitivity	Sw	High gain	14400	18000	-	3520	4400	-	V/Ix · s
		Low gain	7200	9000	-	1760	2200	-	
Photoresponse nonuniformity*9	PRNU	-	-	±10	-	-	±10	%	
Noise*10	N	High gain	-	2.0	3.0	-	1.3	2.0	mV rms
		Low gain	-	1.1	1.7	-	0.7	1.1	
Output offset voltage*11	Voffset	-	Vref	-	-	Vref	-	V	

\*7: Integration time Ts=1 ms

\*8: Measured with a 2856 K tungsten lamp.

\*9: Photoresponse nonuniformity (PRNU) is the output nonuniformity that occurs when the photosensitive area is uniformly illuminated by light which is approx. 50% of the saturation level. PRNU is defined as follows:

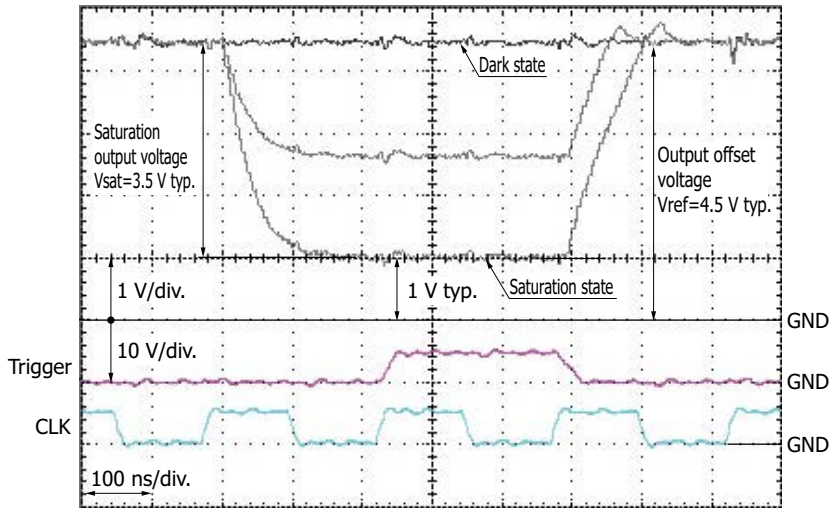
$$PRNU = \Delta X / X \times 100 [\%]$$

X: average output of all elements,  $\Delta X$ : difference between X and the maximum or minimum output, whichever is larger.

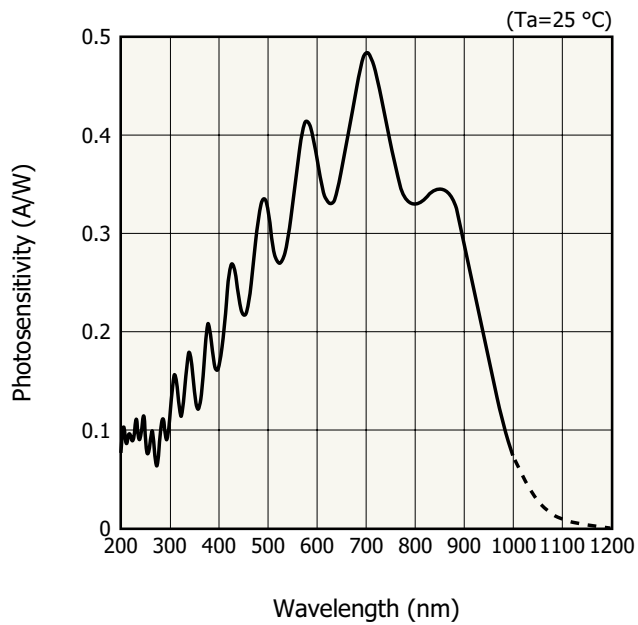
\*10: Measured with a video data rate of 50 kHz and Ts=1 ms in dark state.

\*11: Video output is negative-going output with respect to the output offset voltage.

**Output waveform of one element**

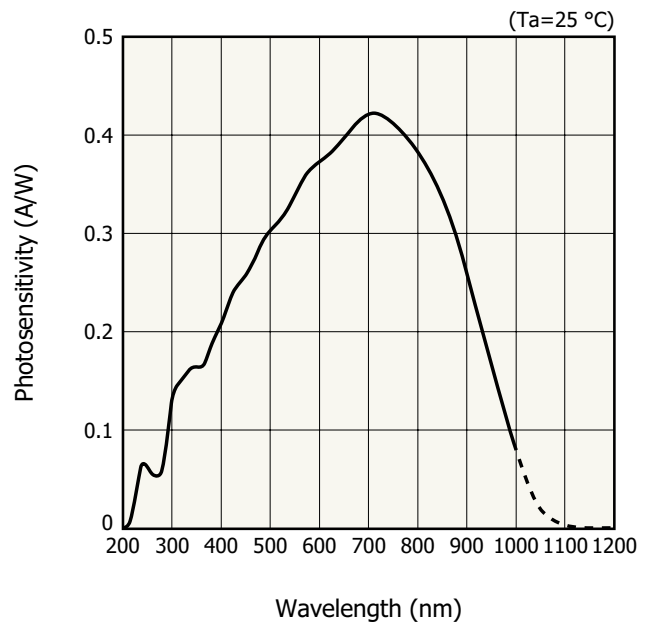


**Spectral response (typical example)**



KMPD80220EB

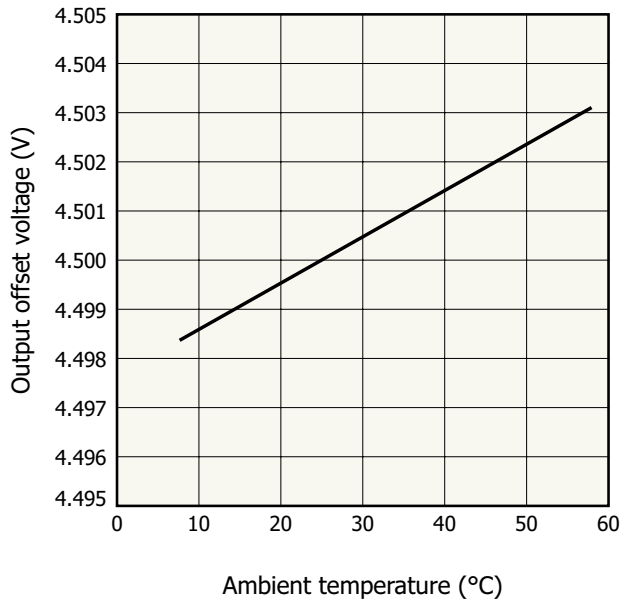
When silicone resin is applied (for attaching a fluorescent screen)



KMPD80421EA

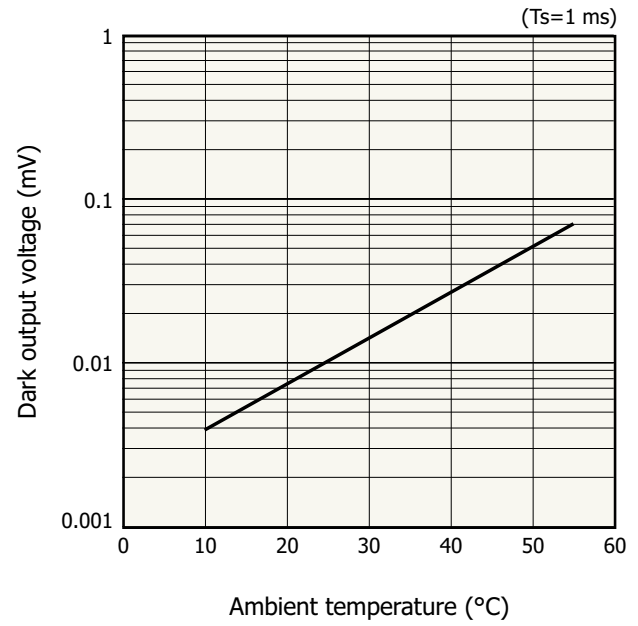
When the fluorescent screen is attached, the spectral response becomes smooth due to the effects of the adhesive resin.

**Output offset voltage vs. ambient temperature (measurement example)**



KMPDB0288EA

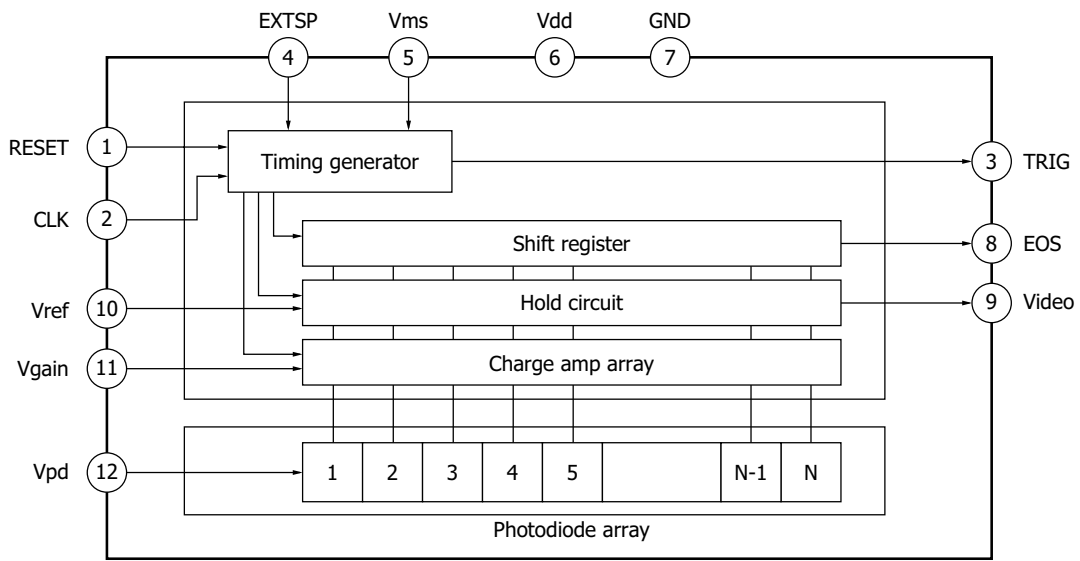
**Dark output voltage vs. ambient temperature (typical example)**



KMPDB0289EB

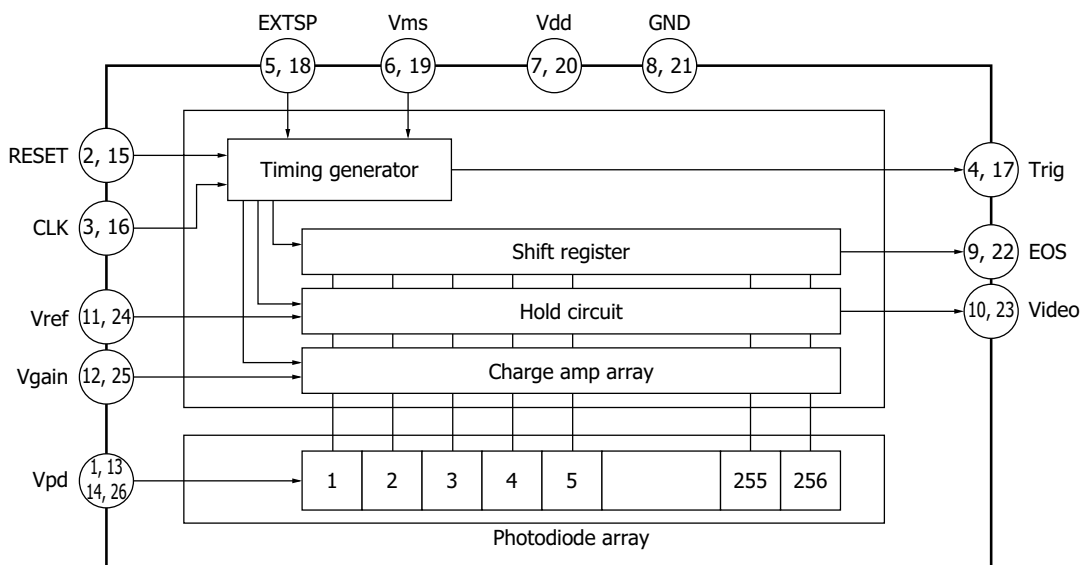
**Block diagram**

S11865-64/-128, S11866-64-02/-128-02



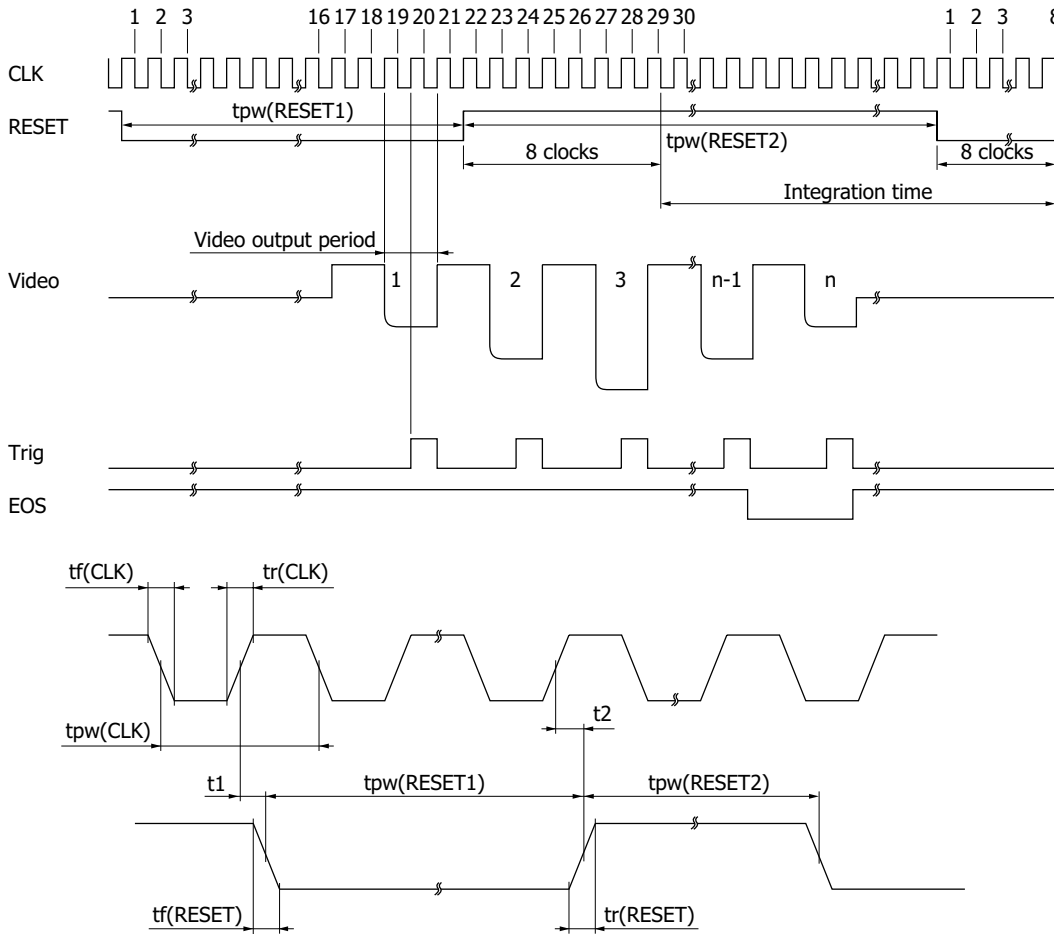
KMPDC0153EA

S11865-256



KMPDC0506EA

**Timing chart**



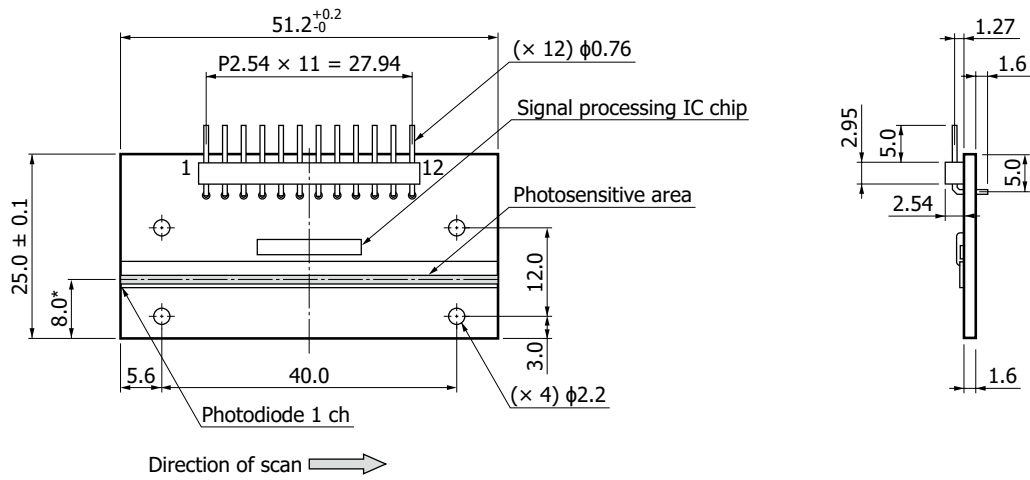
KMPDC0289ED

Parameter	Symbol	Min.	Typ.	Max.	Unit
Clock pulse width	tpw(CLK)	250	-	25000	ns
Clock pulse rise/fall times	tr(CLK), tf(CLK)	0	20	30	ns
Reset pulse width 1	tpw(RESET1)	21	-	-	CLK
Reset pulse width 2	tpw(RESET2)	20	-	-	CLK
Reset pulse rise/fall times	tr(RESET), tf(RESET)	0	20	30	ns
Clock pulse-reset pulse timing 1	t1	-20	0	20	ns
Clock pulse-reset pulse timing 2	t2	-20	0	20	ns

1. The internal timing circuit starts operation at the falling edge of CLK immediately after a RESET pulse goes Low.
2. When the falling edge of each CLK is counted as "1 clock", the video signal of the 1st channel appears between "18.5 clocks and 20.5 clocks". Subsequent video signals appear every 4 clocks.
3. The trigger pulse for the 1st channel rises at a timing of 19.5 clocks and then rises every 4 clocks. The rising edge of each trigger pulse is the recommended timing for data acquisition.
4. Signal charge integration time equals the High period of a RESET pulse. However, the charge integration does not start at the rise of a RESET pulse but starts at the fall of the 8th clock after the rise of the RESET pulse and ends at the fall of the 8th clock after the fall of the RESET pulse.  
After the RESET pulse next changes from High to Low, signals integrated within this period are sequentially read out as time-series signals by the shift register operation. The rise and fall of a RESET pulse must be synchronized with the rise of a CLK pulse, but the rise of a RESET pulse must be set outside the video output period. One cycle of RESET pulses cannot be set shorter than the time equal to "16.5 + 4 × N (number of elements)" clocks.
5. The video signal after an EOS signal output becomes a high impedance state, and the video output will be indefinite.

**Dimensional outlines (unit: mm)**

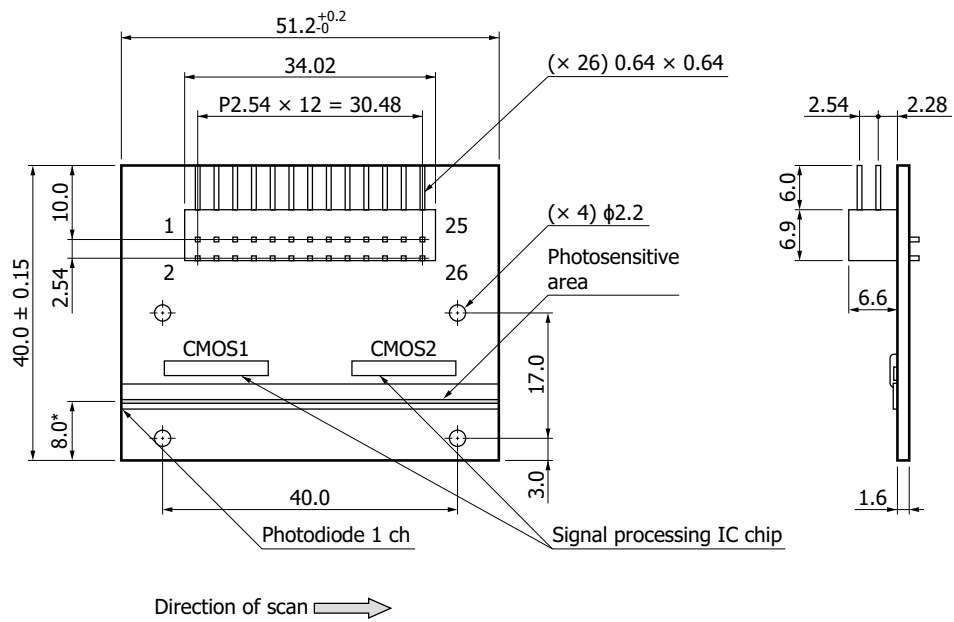
S11865-64/-128



Tolerance unless otherwise noted:  $\pm 0.2$   
 \* Distance from board bottom to photosensitive area center  
 Board: G10 glass epoxy  
 Connector: PRECI-DIP DURTAL 800-10-012-20-001101

KMPDA0164EG

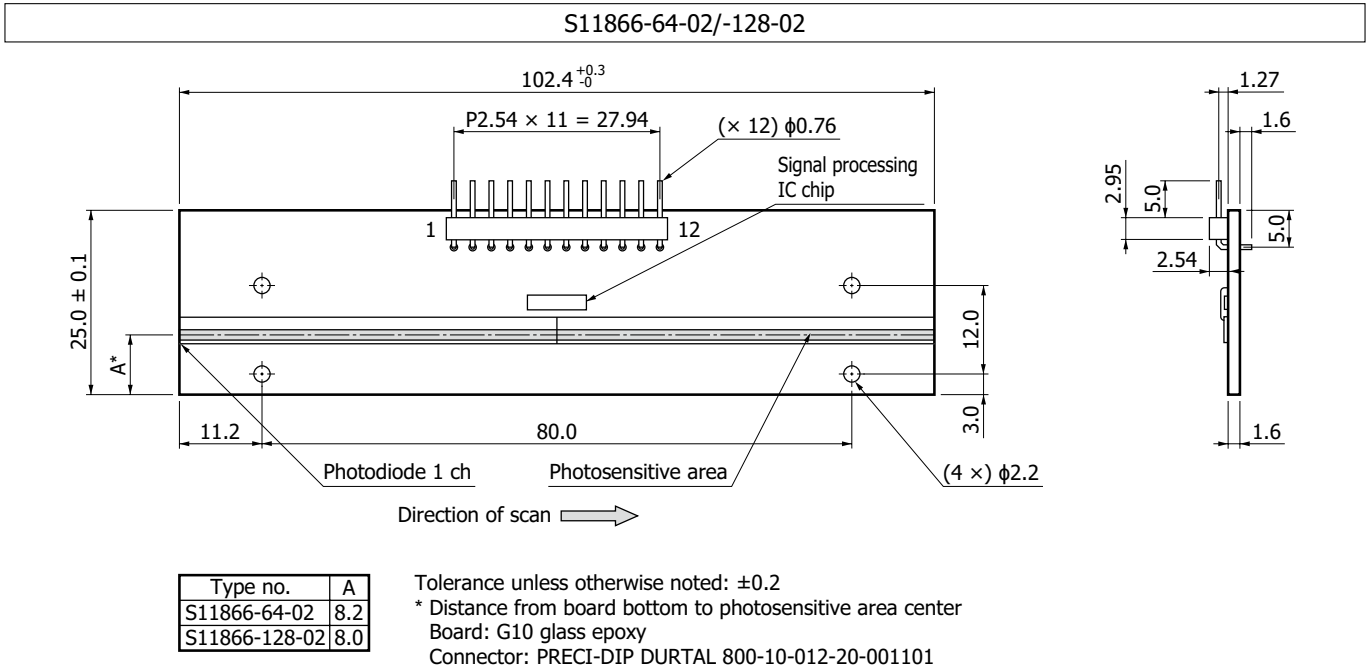
S11865-256



Tolerance unless otherwise noted:  $\pm 0.2$   
 \* Length from board bottom to photosensitive area center  
 Board: G10 glass epoxy  
 Connector: JAE (Japan Aviation Electronics Industry, Limited)  
 PS-26PE-D4LT1-PN1

KMPDA0191EE





KMPDA0291EB

**Pin connections**

S11865-64/-128, S11866-64-02/-128-02

Pin no.	Symbol	Name	Note
1	RESET	Reset pulse	Pulse input
2	CLK	Clock pulse	Pulse input
3	Trig	Trigger pulse	Positive-going pulse output
4	EXTSP	External start pulse	Pulse input
5	Vms	Master/slave selection supply voltage	Voltage input
6	Vdd	Supply voltage	Voltage input
7	GND	Ground	
8	EOS	End of scan	Negative-going pulse output
9	Video	Video output	Negative-going output with respect to Vref
10	Vref	Reference voltage	Voltage input
11	Vgain	Gain selection terminal voltage	Voltage input
12	Vpd	Photodiode voltage	Voltage input

S11865-256

Pin no.	CMOS1	Pin no.	CMOS2	Name	Note
1	Vpd	14	Vpd	Photodiode voltage	Voltage input
2	RESET	15	RESET	Reset pulse	Pulse input
3	CLK	16	CLK	Clock pulse	Pulse input
4	Trig	17	Trig	Trigger pulse	Positive-going pulse output
5	EXTSP	18	EXTSP	External start pulse	Pulse input
6	Vms	19	Vms	Master/slave selection voltage	Voltage input
7	Vdd	20	Vdd	Supply voltage	Voltage input
8	GND	21	GND	Ground	
9	EOS	22	EOS	End of scan	Negative-going pulse output
10	Video	23	Video	Video output	Negative-going output from Vref
11	Vref	24	Vref	Reference voltage	Voltage input
12	Vgain	25	Vgain	Gain selection voltage	Voltage input
13	Vpd	26	Vpd	Photodiode voltage	Voltage input

**Gain selection terminal voltage setting**

Vdd: High gain (Cf=0.5 pF) GND: Low gain (Cf=1 pF)

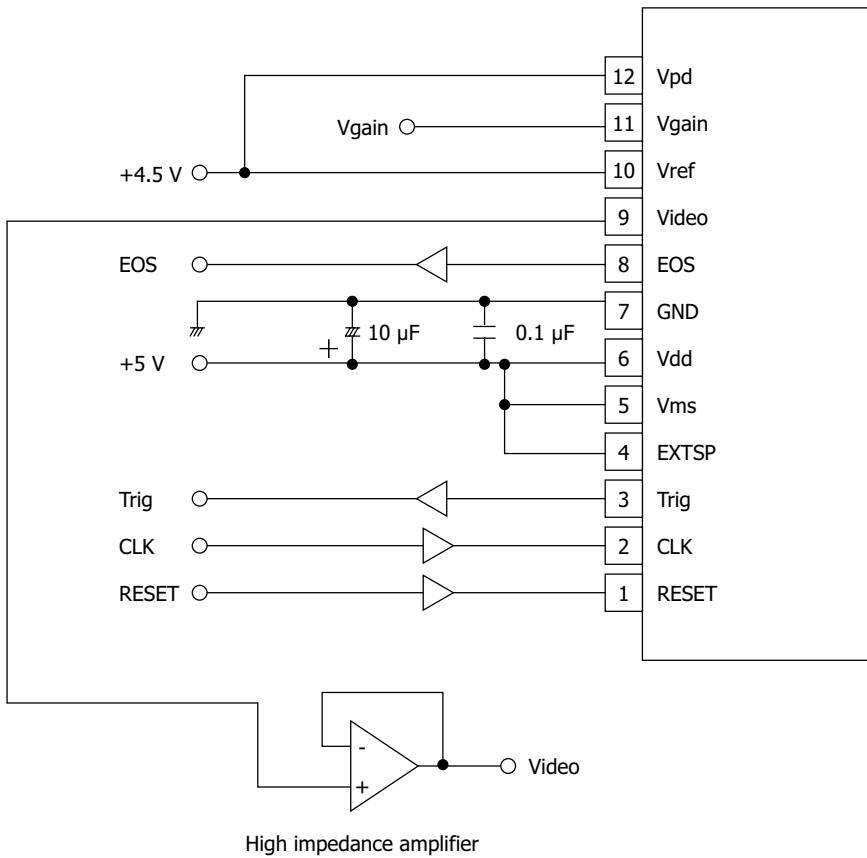
**Setting for each readout method**

S11865-64/-128, S11866-64-02/-128-02

Set to A in the table below in most cases.

To serially read out signals from two or more sensors linearly connected, set the 1st sensor to A and the 2nd or later sensors to B. The CLK and RESET pulses should be shared with each sensor and the video output terminal of each sensor connected together.

■ Connection example (parallel readout)



KMPDC0288EB

Setting	Readout method	Vms	EXTSP
A	All stages of parallel readout, serial readout at 1st sensor	Vdd	Vdd
B	Serial readout at 2nd and later sensors	GND	Preceding sensor EOS should be input

S11865-256

Signals of channels 1 through 126 are output from CMOS1, while signals of channels 129 through 256 are output from CMOS2. The following two readout methods are available.

(1) Serial readout method

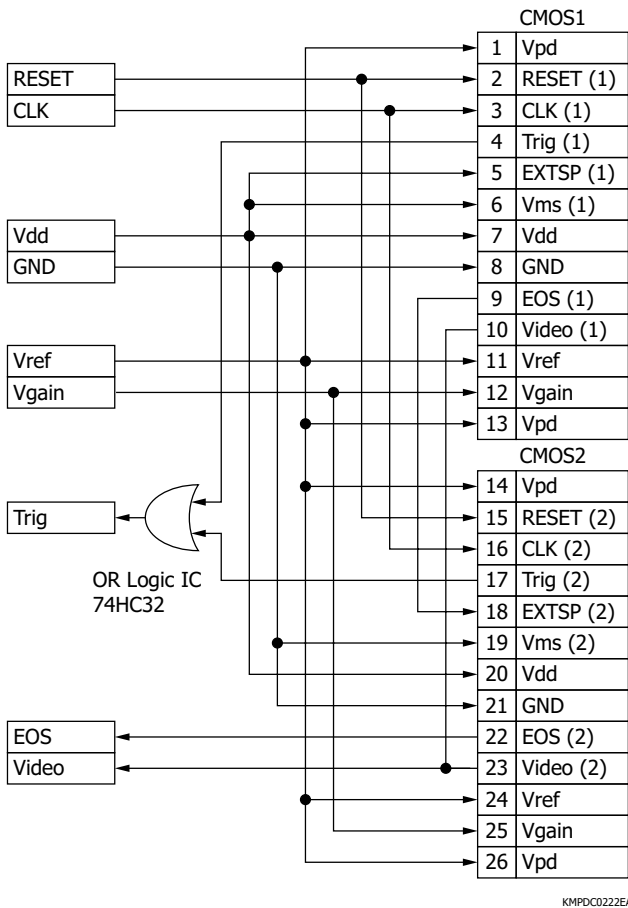
CMOS1 and CMOS2 are connected in serial and the signals of channels 1 through 256 are sequentially read out from one output line. Set CMOS1 as in "A" in the table below, and set CMOS2 as in "B". CMOS1 and CMOS2 should be connected to the same CLK and RESET lines, and their video output terminals to one line.

(2) Parallel readout method

128 channel signals are output in parallel respectively from the output lines of CMOS1 and CMOS2. Set both CMOS1 and CMOS2 as in "A" in the table below.

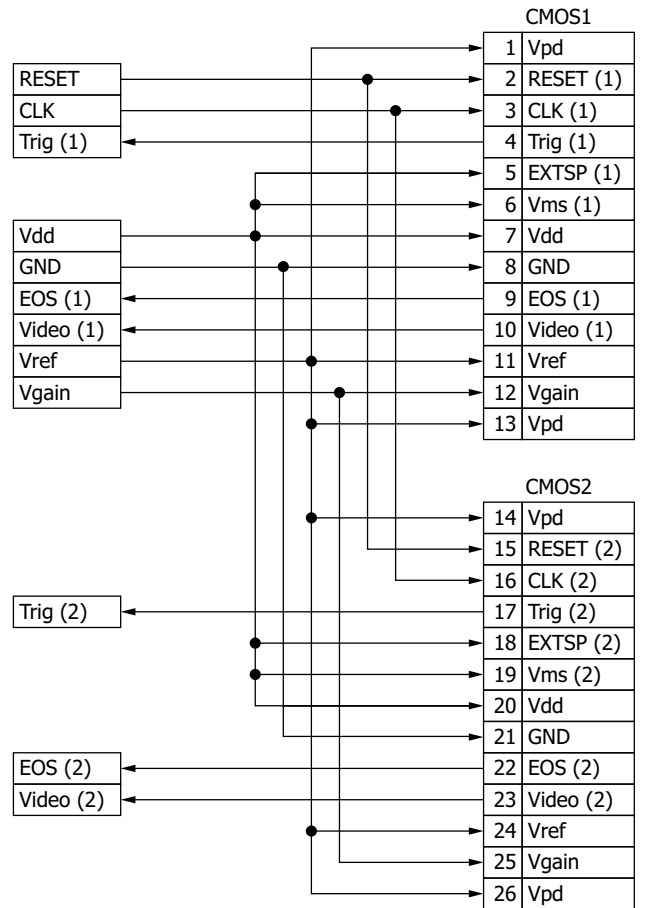
■ Connection examples

· Serial readout method



KMPDC0222EA

· Parallel readout method



KMPDC0223EB

Setting	Vms	EXTSP
A	Vdd	Vdd
B	GND	Preceding sensor EOS should be input

### ❏ Readout circuit

Check that pulse signals meet the required pulse conditions before supplying them to the input terminals. Video output should be amplified by an operational amplifier that is connected close to the sensor.

### ❏ Precautions for use

- (1) The signal processing IC chip is protected against static electricity. However, in order to prevent possible damage to the IC chip, take electrostatic countermeasures such as grounding yourself, as well as workbench and tools. Also protect the IC chip from surge voltages from peripheral equipment.
- (2) Gold wires for wire bonding are very thin, so they easily break if subjected to mechanical stress. The signal processing IC chip and wire bonding section are covered with resin for protection. However, never touch these portions. Excessive force, if applied, may break the wires or cause malfunction.  
Blow air to remove dust or debris if it gets on the protective resin. Never wash them with solvent.  
Signals may not be obtained if dust or debris is left or a scratch is made on the protective resin, or the signal processing IC chip or photodiode array chip is nicked.
- (3) The photodiode array characteristics may deteriorate when operated at high humidity, so put it in a hermetically sealed enclosure or case. When installing the photodiode array on a board, be careful not to cause the board to warp.

### ❏ Related information

[www.hamamatsu.com/sp/ssd/doc\\_en.html](http://www.hamamatsu.com/sp/ssd/doc_en.html)

- Precautions
  - Disclaimer
  - Unsealed products
  - Image sensors

Driver circuit C9118-01 (sold separately)

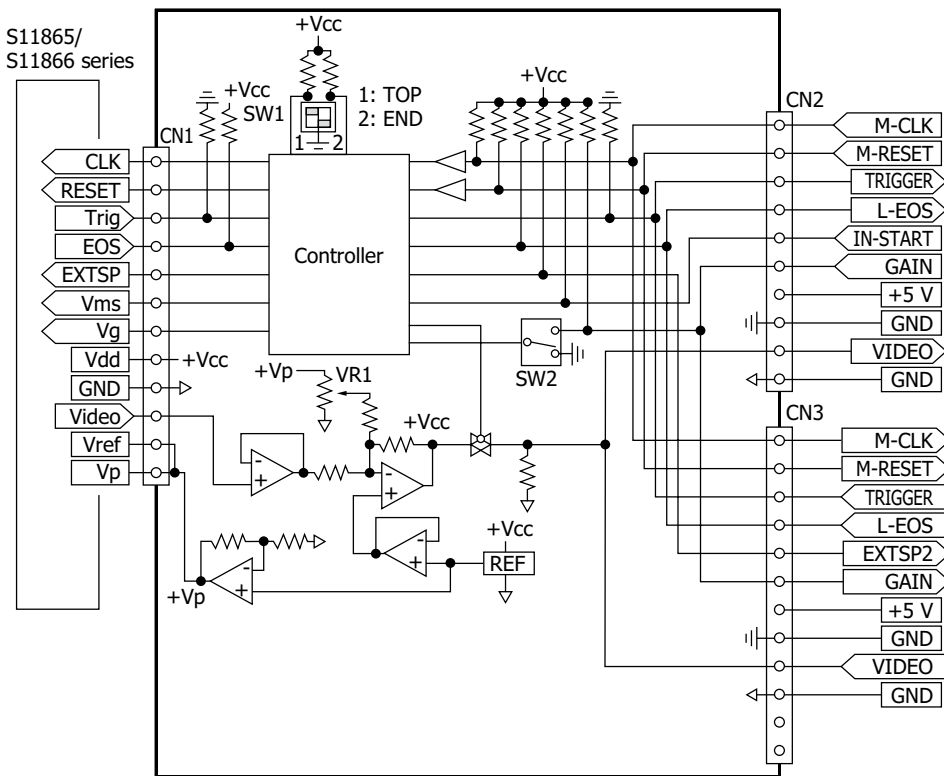
The CMOS driver circuit is designed for S11865/S11866 series photodiode arrays with amplifier. The C9118-01 operates a photodiode by just inputting two signals (M-CLK and M-RESET) and a signal +5 V supply.

**Features**

- Single power supply (+5 V) operation
- Operation with two input signals (M-CLK and M-RESET)
- Compact: 46 × 56 × 5.2 mm



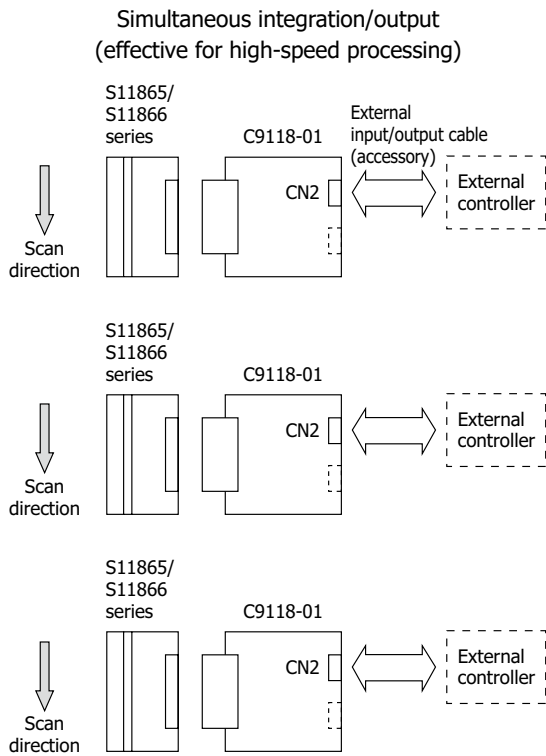
**Block diagram**



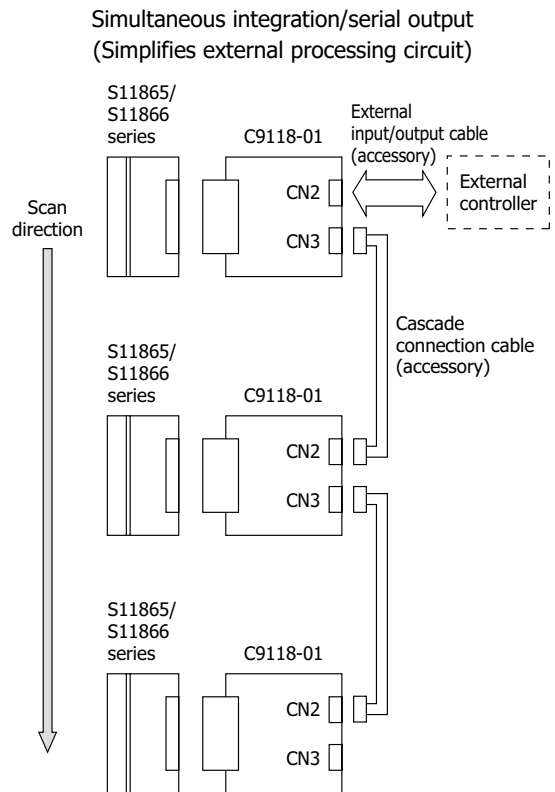
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**Connection examples**

Single or parallel readout example\*



Cascade readout example\*



\* Switch setting is required.

Information described in this material is current as of May 2022.

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